



STW48NM60N

N-channel 600 V, 0.055 Ω typ., 44 A MDmesh™ II Power MOSFET in a TO-247 package

Datasheet — production data

Features

| Order codes | V _{DSS} @ T _{Jmax} | R _{DS(on)} max | I _D |
|-------------|-----------------------------------------|----------------------------|----------------|
| STW48NM60N | 650 V | < 0.07 Ω | 44 A |

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

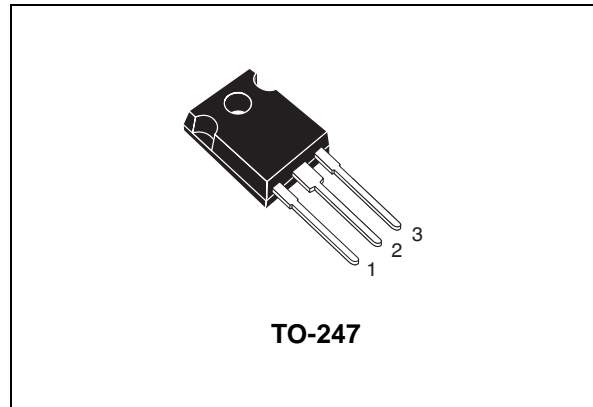


Figure 1. Internal schematic diagram

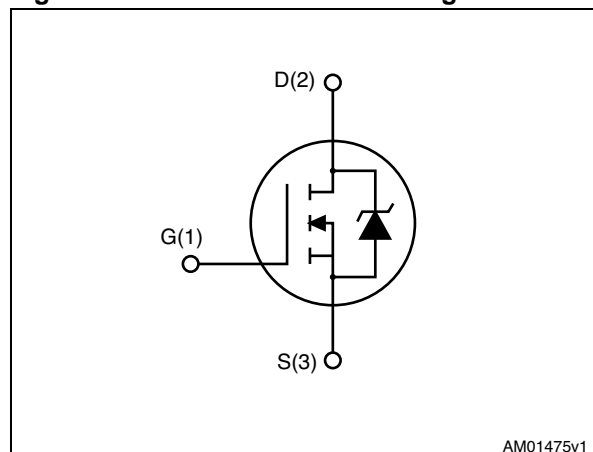


Table 1. Device summary

| Order code | Marking | Package | Packaging |
|------------|---------|---------|-----------|
| STW48NM60N | 48NM60N | TO-247 | Tube |

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1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|----------------------------------------------------------------------------------------------------------------|-------------|------------------|
| V_{DS} | Drain-source voltage | 600 | V |
| V_{GS} | Gate-source voltage | ± 25 | V |
| I_D | Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$ | 44 | A |
| I_D | Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$ | 28 | A |
| $I_{DM}^{(1)}$ | Drain current (pulsed) | 176 | A |
| P_{TOT} | Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ | 330 | W |
| I_{AS} | Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max) | 8 | A |
| E_{AS} | Single pulse avalanche energy (starting $T_j=25\text{ }^\circ\text{C}$, $I_D=I_{AS}$, $V_{DD}=50\text{ V}$) | 457 | mJ |
| $dv/dt^{(2)}$ | Peak diode recovery voltage slope | 15 | V/ns |
| T_{stg} | Storage temperature | - 55 to 150 | $^\circ\text{C}$ |
| T_j | Max. operating junction temperature | 150 | $^\circ\text{C}$ |

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 44\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS\text{ peak}} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 3. Thermal data

| Symbol | Parameter | Value | Unit |
|----------------|------------------------------------------------|-------|---------------------------|
| $R_{thj-case}$ | Thermal resistance junction-case max | 0.38 | $^\circ\text{C}/\text{W}$ |
| $R_{thj-amb}$ | Thermal resistance junction-ambient max | 50 | $^\circ\text{C}/\text{W}$ |
| T_l | Maximum lead temperature for soldering purpose | 300 | $^\circ\text{C}$ |

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified).

Table 4. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--------------------------------------------------|-------------------------------------------------------------------------|------|-------|-----------|--------------------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage ($V_{GS} = 0$) | $I_D = 1\text{ mA}$ | 600 | | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = 600\text{ V}$ $V_{DS} = 600\text{ V}, T_c = 125\text{ °C}$ | | | 1 100 | μA μA |
| I_{GSS} | Gate-body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 25\text{ V}$ | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2 | 3 | 4 | V |
| $R_{DS(on)}$ | Static drain-source on-resistance | $V_{GS} = 10\text{ V}, I_D = 20\text{ A}$ | | 0.055 | 0.07 | Ω |

Table 5. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|----------------------------|-------------------------------|-------------------------------------------------------------------------------------------|------|------|------|----------|
| C_{iss} | Input capacitance | $V_{DS} = 50\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$ | - | 4285 | - | pF |
| C_{oss} | Output capacitance | | | 212 | | pF |
| C_{rss} | Reverse transfer capacitance | | | 9.5 | | pF |
| $C_{oss\text{ eq.}}^{(1)}$ | Equivalent output capacitance | $V_{GS} = 0, V_{DS} = 0\text{ to }480\text{ V}$ | - | 600 | - | pF |
| R_g | Intrinsic gate resistance | $f = 1\text{ MHz}, V_{GS} = 0$ | | 1.6 | | Ω |
| Q_g | Total gate charge | $V_{DD} = 480\text{ V}, I_D = 44\text{ A},$ $V_{GS} = 10\text{ V},$ (see Figure 15) | - | 124 | - | nC |
| Q_{gs} | Gate-source charge | | | 20 | | nC |
| Q_{gd} | Gate-drain charge | | | 61.5 | | nC |

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}

Table 6. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------|---------------------|------------------------------------------------------------------------------------------------------------------|------|------|------|------|
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 300\text{ V}, I_D = 20\text{ A}$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 14) | - | 99 | - | ns |
| t_r | Rise time | | | 18 | | ns |
| $t_{d(off)}$ | Turn-off delay time | | | 214 | | ns |
| t_f | Fall time | | | 25.5 | | ns |

Table 7. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|-------------------------------|------------------------------------------------------------|------|------|------|---------------|
| I_{SD} | Source-drain current | | - | | 44 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | - | | 176 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 44 \text{ A}, V_{GS} = 0$ | - | | 1.6 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 44 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ | - | 472 | | ns |
| Q_{rr} | Reverse recovery charge | $V_{DD} = 100 \text{ V}$ | - | 10.5 | | μC |
| I_{RRM} | Reverse recovery current | (see Figure 16) | - | 44.5 | | A |
| t_{rr} | Reverse recovery time | $I_{SD} = 44 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ | - | 568 | | ns |
| Q_{rr} | Reverse recovery charge | $V_{DD} = 100 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$ | - | 14 | | μC |
| I_{RRM} | Reverse recovery current | (see Figure 16) | - | 50 | | A |

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

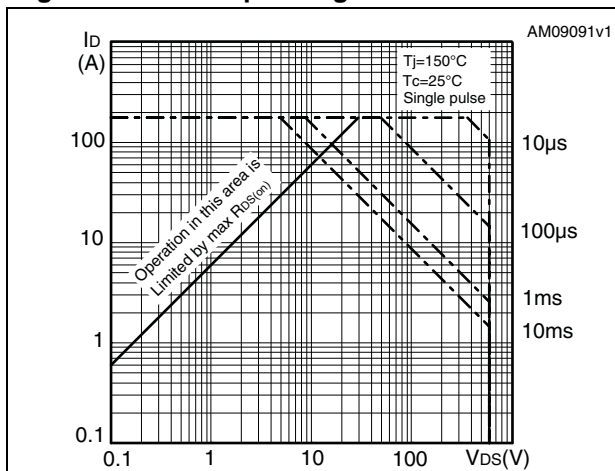


Figure 3. Thermal impedance

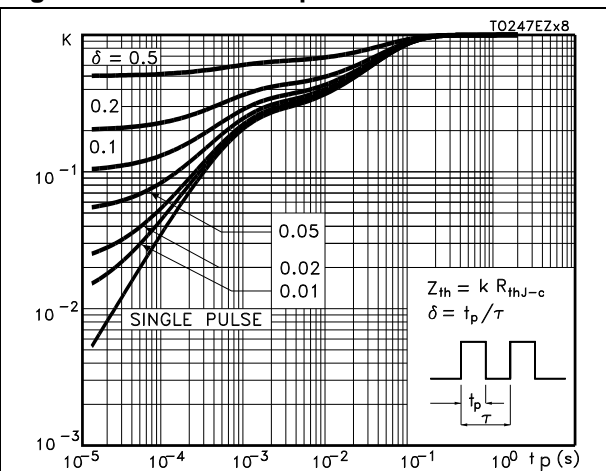


Figure 4. Output characteristics

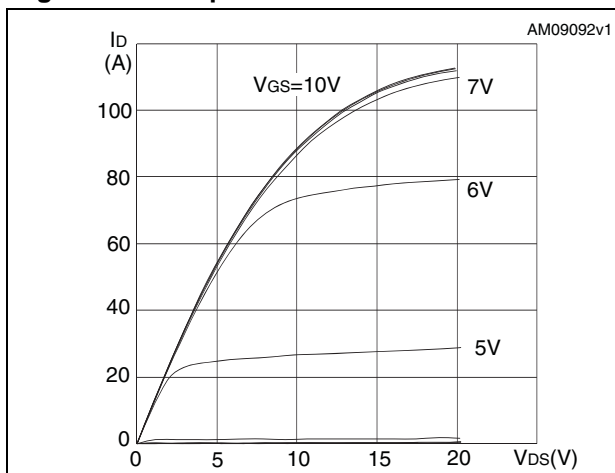


Figure 5. Transfer characteristics

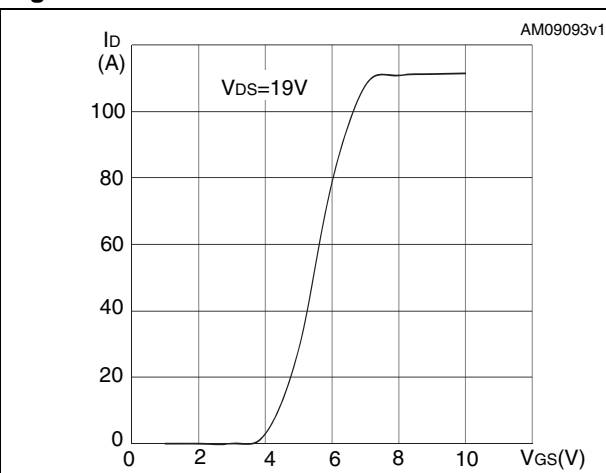


Figure 6. Normalized BV_{DSS} vs temperature

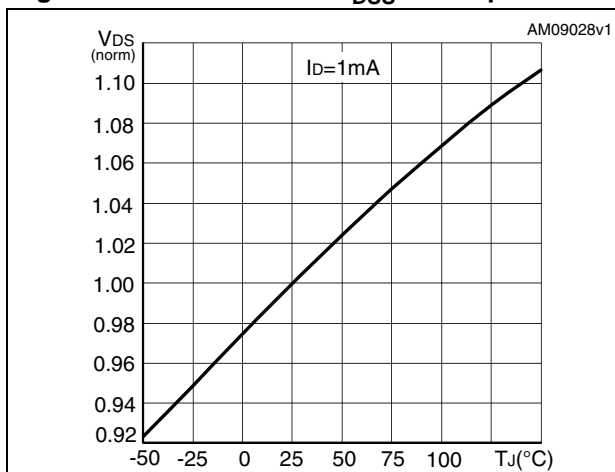


Figure 7. Static drain-source on-resistance

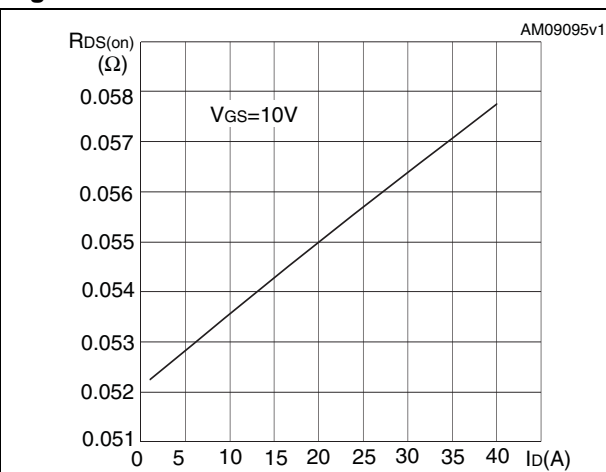


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

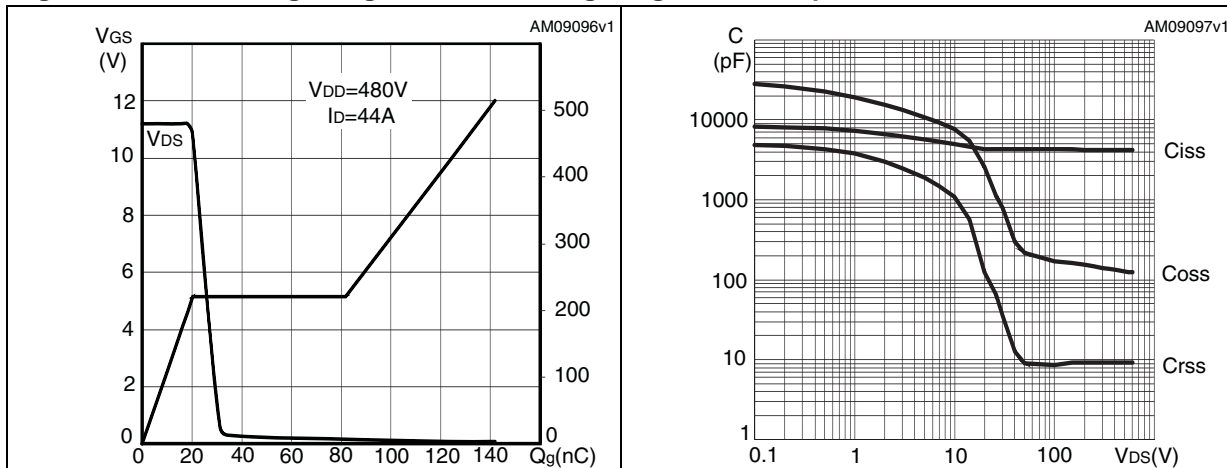


Figure 10. Output capacitance stored energy Figure 11. Normalized gate threshold voltage vs temperature

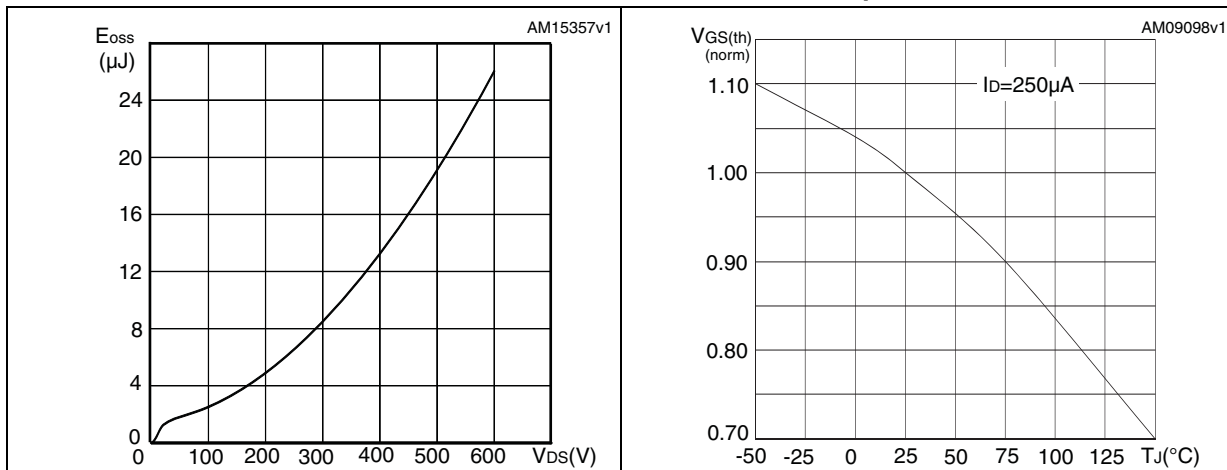
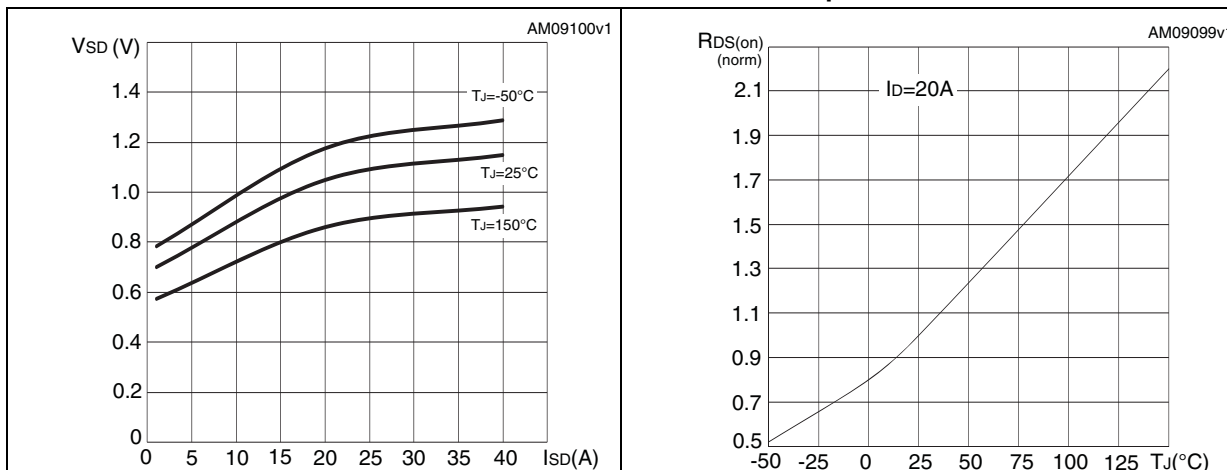


Figure 12. Source-drain diode forward characteristics Figure 13. Normalized on-resistance vs temperature



3 Test circuits

Figure 14. Switching times test circuit for resistive load

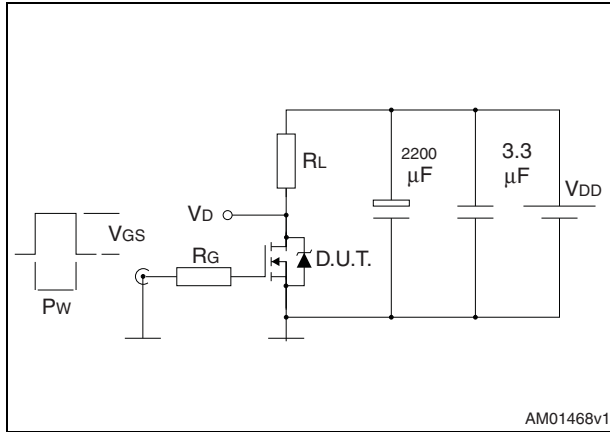


Figure 15. Gate charge test circuit

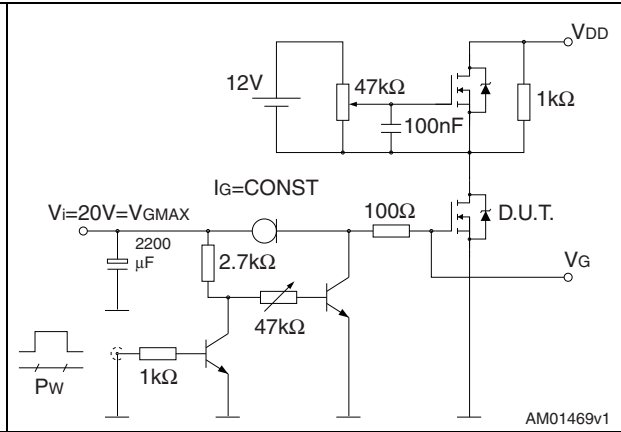


Figure 16. Test circuit for inductive load switching and diode recovery times

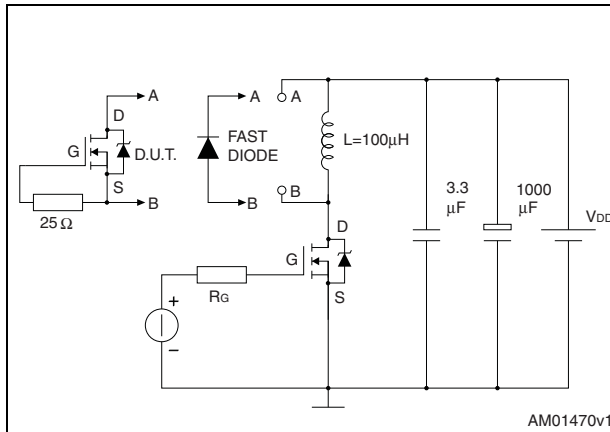


Figure 17. Unclamped inductive load test circuit

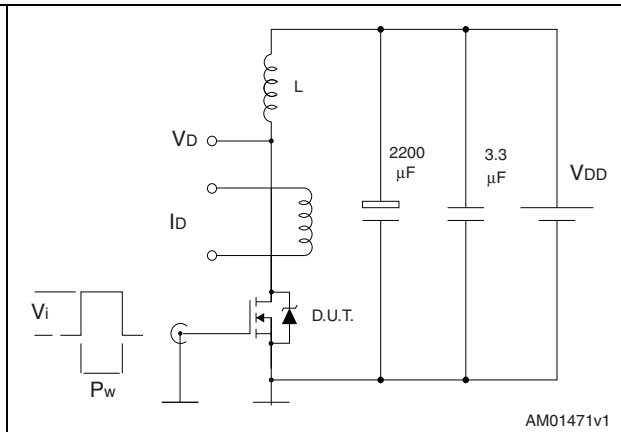


Figure 18. Unclamped inductive waveform

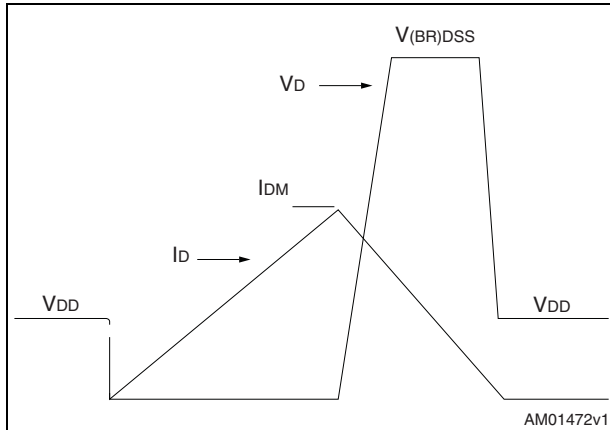
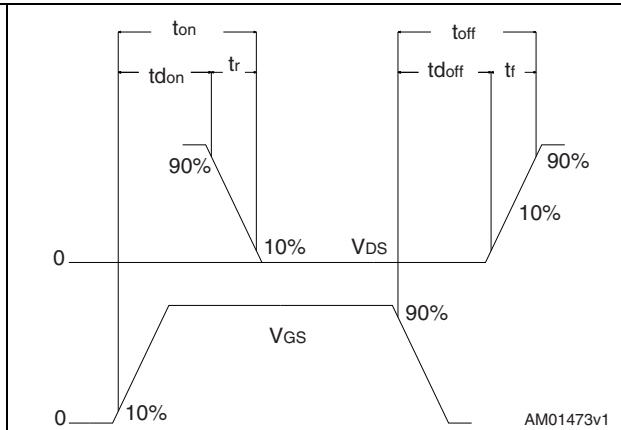


Figure 19. Switching time waveform



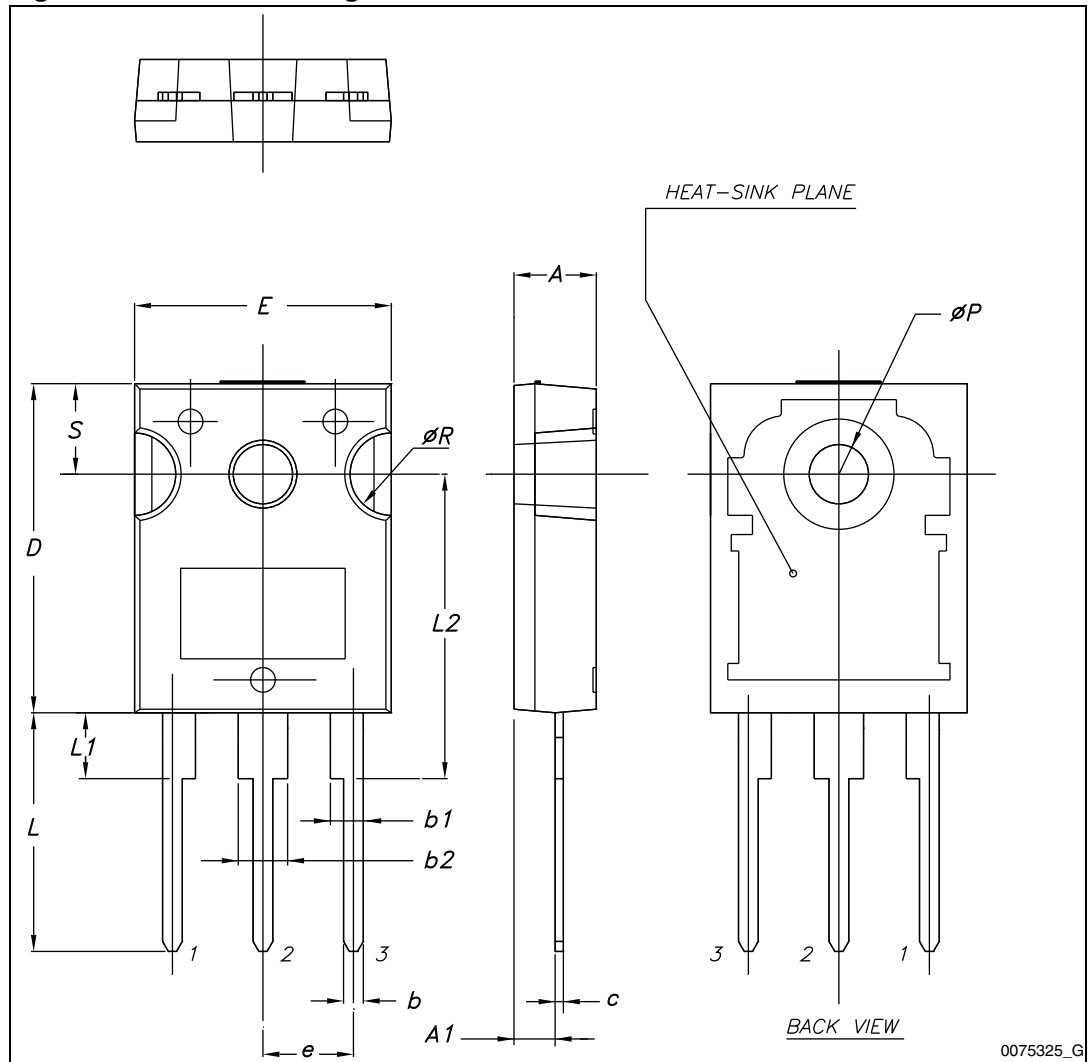
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Table 8. TO-247 mechanical data

| Dim. | mm. | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.85 | | 5.15 |
| A1 | 2.20 | | 2.60 |
| b | 1.0 | | 1.40 |
| b1 | 2.0 | | 2.40 |
| b2 | 3.0 | | 3.40 |
| c | 0.40 | | 0.80 |
| D | 19.85 | | 20.15 |
| E | 15.45 | | 15.75 |
| e | 5.30 | 5.45 | 5.60 |
| L | 14.20 | | 14.80 |
| L1 | 3.70 | | 4.30 |
| L2 | | 18.50 | |
| ØP | 3.55 | | 3.65 |
| ØR | 4.50 | | 5.50 |
| S | 5.30 | 5.50 | 5.70 |

Figure 20. TO-247 drawing



5 Revision history

Table 9. Document revision history

| Date | Revision | Changes |
|-------------|----------|---------------------------------------------------------------------------------------------------------------------------------------------|
| 06-Dec-2010 | 1 | First release. |
| 15-Apr-2011 | 2 | Document status promoted from preliminary data to datasheet. |
| 04-Jul-2011 | 3 | Updated Figure 7 . |
| 10-Oct-2012 | 4 | – Modified: Figure 2 – Added: Figure 10 – Updated: Section 4: Package mechanical data |
| 19-Feb-2013 | 5 | Updated Table 7: Source drain diode . |

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